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#### What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

Betano	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	20MHz
Connectivity	CSI, I <sup>2</sup> C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	10
Program Memory Size	2KB (2K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256 x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 5.5V
Data Converters	A/D 7x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	16-SSOP (0.173", 4.40mm Width)
Supplier Device Package	16-SSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10y46asp-30

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

#### O ROM, RAM capacities

Flash ROM	RAM	10 pins	16 pins
4 KB	512 B	-	R5F10Y47ASP Note 2
2 KB	256 B	R5F10Y16ASP	R5F10Y46ASP Note 2
1 KB	128 B	R5F10Y14ASP	R5F10Y44ASP Note 2

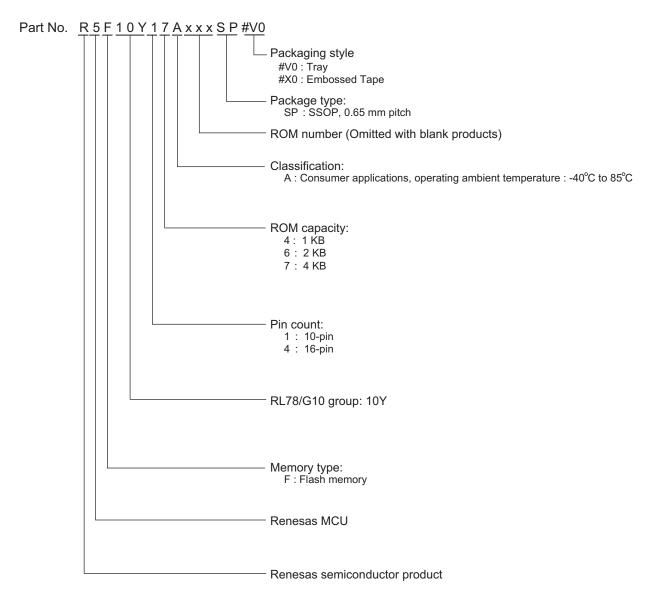
Notes 1. 16-pin products only

2. Under development

Remark The functions mounted depend on the product. See 1.6 Outline of Functions.



## 1.2 List of Part Number



#### Figure 1-1. Classification of Part Number

Pin count	Package	Part Number		
10 pins	10-pin plastic LSSOP	R5F10Y16ASP#V0, R5F10Y16ASP#X0		
	$(4.4 \times 3.6 \text{ mm}, 0.65 \text{mmpitch})$	R5F10Y14ASP#V0, R5F10Y14ASP#X0		
16 pins	16-pin plastic SSOP	R5F10Y47ASP Note		
	$(4.4 \times 5.0 \text{ mm}, 0.65 \text{mmpitch})$	R5F10Y46ASP Note		
		R5F10Y44ASP Note		

**Note** Under development

Caution The part number represents the number at the time of publication. Be sure to review the latest part number through the target product page in the Renesas Electronics Corp.website.



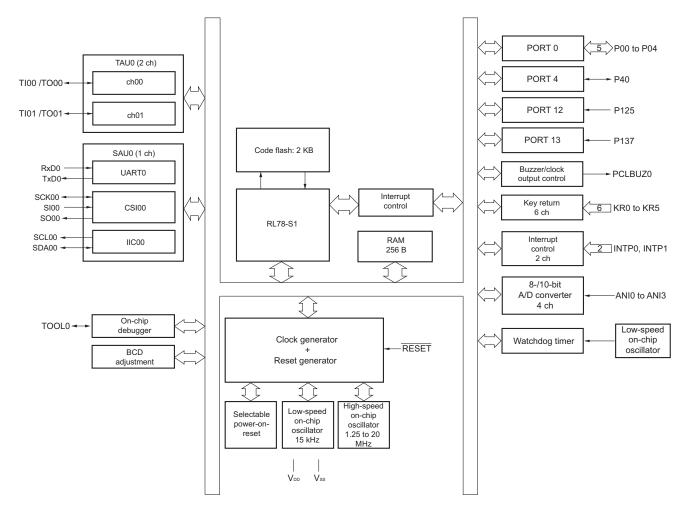
## 1.4 Pin Identification

ANI0 to ANI6	: Analog Input
INTP0 to INTP3	: External Interrupt Input
KR0 to KR5	: Key Return
P00 to P07	: Port 0
P40, P41	: Port 4
P121, P122, P125	: Port 12
P137	: Port 13
PCLBUZ0	: Programmable Clock Output/ Buzzer Output
EXCLK	: External Clock Input
X1, X2	: Crystal Oscillator
IVCMP0	: Comparator Input
VCOUT0	: Comparator Output
IVREF0	: Comparator Reference Input
RESET	: Reset
RxD0	: Receive Data
SCK00, SCK01	: Serial Clock Input/Output
SCL00, SCLA0	: Serial Clock Output
SDA00, SDAA0	: Serial Data Input/Output
SI00, SI01	: Serial Data Input
SO00, SO01	: Serial Data Output
TI00 to TI03	: Timer Input
TO00 to TO03	: Timer Output
TOOL0	: Data Input/Output for Tool
TxD0	: Transmit Data
Vdd	: Power Supply
Vss	: Ground



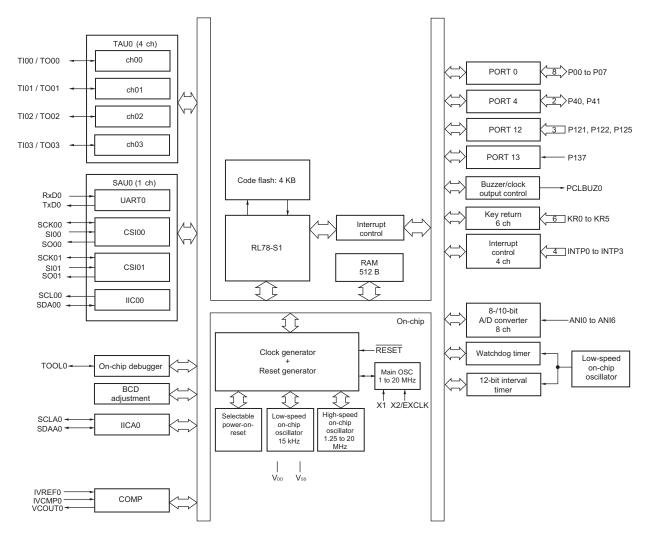
# 1.5 Block Diagram

# 1.5.1 10-pin products





## 1.5.2 16-pin products





## 1.6 Outline of Functions

This outline describes the function at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

Item			10-pin	16-pin				
		R5F10Y16ASP	R5F10Y14ASP	R5F10Y47ASP	R5F10Y46ASP	R5F10Y44ASP		
Code flash	memory	2 KB	1 KB	4 KB	2 KB	1 KB		
RAM	-	256 B 128 B 512 B 256 B				128 B		
Main system clock	High-speed system clock	_	X1, X2 (crystal/ceramic) oscillation       main system clock input (EXCLK)       1 to 20 MHz: VDD = 2.7 to 5.5 V       1 to 5 MHz: VDD = 2.0 to 5.5 V					
	High-speed on-chip oscillator clock	<ul> <li>1.25 to 20 MHz (V</li> <li>1.25 to 5 MHz (VD</li> </ul>	,					
Low-speed clock	on-chip oscillator	15 kHz (TYP)						
General-pu	rpose register	8-bit register × 8						
Minimum in time	struction execution	0.05 μs (20 MHz ope	eration)					
Instruction s	set	<ul><li>Multiplication (8 bit</li><li>Rotate, barrel shift</li></ul>	tor/logical operation (8 bi					
I/O port	Total	8	. ,	14				
·	CMOS I/O	6 (N-ch open-drain o	utput (VDD tolerance): 2)	10 (N-ch open-	drain output (VDD	tolerance): 4)		
	CMOS input	2	· · · · · · · · ·	4	1 (	, ,		
Timer	16-bit timer	2 channels		4 channels				
	Watchdog timer	1 channel						
	12-bit interval timer	_		1 channel				
	Timer output	2 channels (PWM ou	itput: 1)	4 channels (PW	/M outputs: 3 <sup>Note 1</sup> )			
Clock outpu	it/buzzer output	1						
		2.44 kHz to 10 MHz:	(Peripheral hardware clo	ck: fmain = 20 MHz (	operation)			
Comparato	ſ			1				
8-/10-bit res	solution A/D converter	4 channels		8 channels				
Serial interf	ace	[10-pin products] CSI: 1 channel/simplified I <sup>2</sup> C: 1 channel/UART: 1 channel						
		[16-pin products] CS	I: 2 channels/simplified I <sup>2</sup>	C: 1 channel/UART	: 1 channel			
	I <sup>2</sup> C bus	—		1 channel				
Vectored	Internal	8		14				
interrupt sources	External	3		5				
Key interrup	ot	6						
Reset		<ul> <li>Reset by RESET pin</li> <li>Internal reset by watchdog timer</li> <li>Internal reset by selectable power-on-reset</li> <li>Internal reset by illegal instruction execution <sup>Note 2</sup></li> <li>Internal reset by data retention lower limit voltage</li> </ul>						
Selectable I	power-on-reset circuit	Detection voltage: 2.		<u> </u>				
	oug function	Provided						
Power supp	-	VDD = 2.0 to 5.5 V						
	imbient temperature	$T_A = -40 \text{ to } + 85 \text{ °C}$						



# 2. ELECTRICAL SPECIFICATIONS

- Cautions 1. This chapter explains the electrical specifications of two products, the R5F10Y16ASP and the R5F10Y14ASP.
  - 2. Electrical specifications for the 16-pin products are T. B. D. because these products are under development.
  - 3. The RL78/G10 has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
  - 4. The pins mounted depend on the product. Refer to 2.1 Port Functions and 2.2.1 Functions for each product in the RL78/G10 User's Manual.



## 2.1 Absolute Maximum Ratings

#### (T<sub>A</sub> = 25°C)

Parameter	Symbols	Co	onditions	Ratings	Unit
Supply Voltage	VDD			-0.5 to +6.5	V
Input Voltage	VI1			$-0.3$ to V <sub>DD</sub> + $0.3^{Note}$	V
Output Voltage	V <sub>01</sub>			-0.3 to Vdd + 0.3	V
Output current, high	Іон1	Per pin		-40	mA
		Total of all pins	P40	-40	mA
		-140 mA	P00 to P04	-100	mA
Output current, low	IOL1	Per pin		40	mA
		Total of all pins	P40	40	mA
		140 mA	P00 to P04	100	mA
Operating ambient temperature	TA			-40 to +85	°C
Storage temperature	Tstg			-65 to +150	°C

Note Must be 6.5 V or lower.

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
  - 2. The reference voltage is Vss.

#### 2.2 Oscillator Characteristics

#### 2.2.1 On-chip oscillator characteristics

## $(T_A = -40 \text{ to } +85^{\circ}C, 2.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator oscillation clock frequency Notes 1, 2	fін		1.25		20	MHz
High-speed on-chip oscillator oscillation		TA = -20 to +85°C	-2.0		+2.0	%
clock frequency accuracy		TA = -40 to -20°C	-3.0		+3.0	%
Low-speed on-chip oscillator oscillation clock frequency Note 3	fı∟			15		kHz
Low-speed on-chip oscillator oscillation clock frequency accuracy			-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 2 of option byte (000C2H).

- 2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.
- 3. This only indicates the oscillator characteristics.



- Total output current of pins =  $(I_{OH} \times 0.7)/(n \times 0.01)$ <Example> Where n = 80 % and  $I_{OH}$  = - 10.0 mA Total output current of pins = (- 10.0 × 0.7)/(80 × 0.01)  $\cong$  - 8.7 mA
- Total output current of pins =  $(I_{OL} \times 0.7)/(n \times 0.01)$ <Example> Where n = 80 % and  $I_{OL}$  = 10.0 mA Total output current of pins =  $(10.0 \times 0.7)/(80 \times 0.01) \cong 8.7$  mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

- 4. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.
- 5. The value under the condition which satisfies the high-level output current (IOH1).
- 6. The value under the condition which satisfies the low-level output current (IoL1).

## Cautions 1. P00 and P01 do not output high level in N-ch open-drain mode.

- 2. The maximum value of V  ${\ensuremath{\mathsf{H}}}$  of P00 and P01 is V  ${\ensuremath{\mathsf{DD}}}$  even in N-ch open-drain mode.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port.



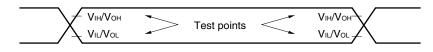
# 2.4 AC Characteristics

(	$T_{A} = -40$ to	+85°C. 2.	0 V <	VDD < 5.5	V, Vss = 0 V	1
	1 = -40 10	+05 0, 2		VDD <u>3</u> 3.3	<b>v</b> , <b>v</b> 33 <b>– 0 v</b>	,

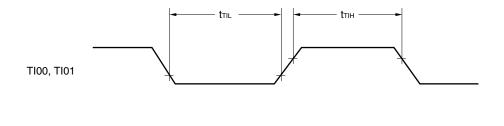
Items	Symbol	Condi	tions	MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Тсч	Main system clock	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	0.05		0.8	μs
instruction execution time)		(fmain) operation	$2.0~V \leq V_{\text{DD}} \leq 5.5~V$	0.2		0.8	μs
TI00, TI01 input high-level width, low-level width	t⊓∺, t⊓∟	Noise filter is not used		1/fмск + 10			ns
TO00, TO01 output frequency	fто	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			10	MHz
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}$				5	MHz
		$2.0~V \leq V_{\text{DD}} < 2.7~V$				2.5	MHz
PCLBUZ0 output frequency	<b>f</b> PCL	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$				10	MHz
		$2.7~V \leq V_{\text{DD}} < 4.0~V$				5	MHz
	$2.0 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$				2.5	MHz	
RESET low-level width	trsl			10			μs

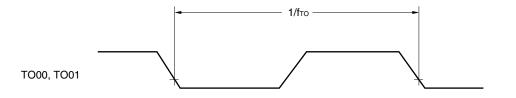
Remark fmck: Timer array unit operation clock frequency

## AC Timing Test Points



#### **TI/TO Timing**







## 2.5 Serial Communication Characteristics

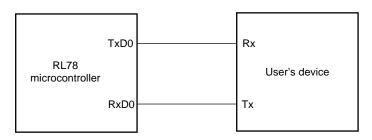
## 2.5.1 Serial array unit

### (1) UART mode

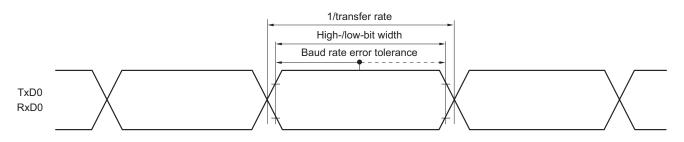
## $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate					fмск/6	bps
		Theoretical value of the maximum transfer rate $f_{CLK} = f_{MCK} = 20 \text{ MHz}$			3.3	Mbps

#### UART mode connection diagram



#### UART mode bit width (reference)



Remarkfмск: Serial array unit operation clock frequency<br/>(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).<br/>m: Unit number, n: Channel number (mn = 00))



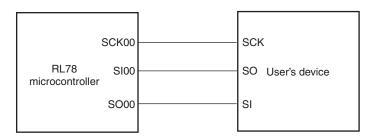
Parameter	Symbol	Condit	tions	MIN.	TYP.	MAX.	Unit
SCKp cycle time	<b>t</b> ксү2	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	fмск = 20 MHz	8/fмск			ns
			fмск ≤ 10 MHz	6/fмск			ns
		$2.0~V \leq V_{\text{DD}} < 2.7~V$		6/fмск			ns
SCKp high-/low-level width	tкн2,	$2.0~V \leq V_{\text{DD}} \leq 5.5~V$		tксү2/2			ns
	tkl2						
SIp setup time (to SCKp^)^{Note 1}	tsik2	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		1/fмск+			ns
				20			
		$2.0~V \leq V_{\text{DD}} < 2.7~V$		1/fмск+			ns
SIp hold time (from SCKp $\uparrow$ ) <sup>Note 2</sup>	tksi2	$2.0~V \leq V_{\text{DD}} \leq 5.5~V$		1/fмск+			ns
				31			
Delay time from SCKp $\downarrow$ to SOp	tĸso2	C = 30 pF Note 4	$2.7~V \leq V_{\text{DD}} \leq 5.5$			2/fмск+50	ns
output Note 3			V				
			$2.0~V \leq V_{\text{DD}} < 2.7$			2/fмск+110	ns
			V				

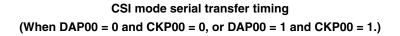
#### (3) CSI mode (slave mode, SCKp... external clock input) (T<sub>A</sub> = -40 to $+85^{\circ}$ C, 2.0 V $\leq$ V<sub>DD</sub> $\leq$ 5.5 V, V<sub>SS</sub> = 0 V)

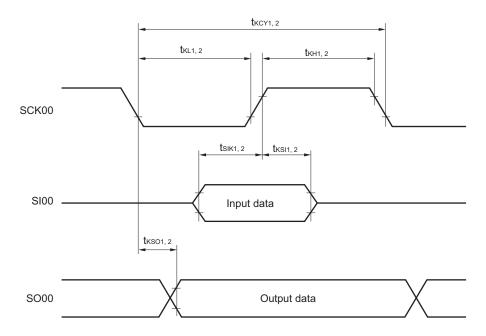
- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
  - **2.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp $\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
  - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp<sup>↑</sup>" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
  - 4. C is the load capacitance of the SOp output lines.
- **Remarks 1.** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0)
  - fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))



#### CSI mode connection diagram

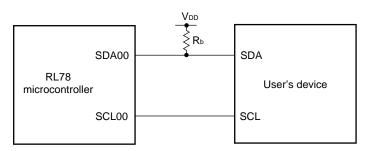




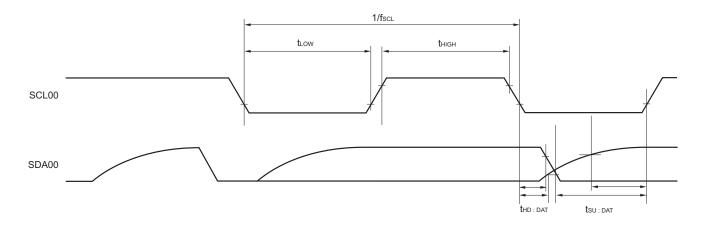




# Simplified I<sup>2</sup>C mode connection diagram



# Simplified I<sup>2</sup>C mode serial transfer timing





## 2.6 Analog Characteristics

## 2.6.1 A/D converter characteristics

#### (Target ANI pin : ANI0 to ANI3)

## $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Co	nditions	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		10	bit
Overall error <sup>Note 1</sup>	AINL	10-bit resolution	$V_{DD} = 5 V$		±1.7	±3.1 Note 2	LSB
			Vdd = 3 V		±2.3	±4.5 <sup>Note 2</sup>	LSB
Conversion time	<b>t</b> CONV	10-bit resolution	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.4		18.4	μs
			$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	4.6		18.4	μs
Zero-scale error <sup>Note 1</sup>	Ezs	10-bit resolution	$V_{DD} = 5 V$			±0.19 <sup>Note 2</sup>	%FSR
			Vdd = 3 V			±0.39 <sup>Note 2</sup>	%FSR
Full-scale error <sup>Note 1</sup>	EFS	10-bit resolution	$V_{DD} = 5 V$			±0.29 <sup>Note 2</sup>	%FSR
			Vdd = 3 V			±0.42 <sup>Note 2</sup>	%FSR
Integral linearity error <sup>Note 1</sup>	ILE	10-bit resolution	$V_{DD} = 5 V$			±1.8 <sup>Note 2</sup>	LSB
			V <sub>DD</sub> = 3 V			±1.7 <sup>Note 2</sup>	LSB
Differential linearity error <sup>Note 1</sup>	DLE	10-bit resolution	Vdd = 5 V			±1.4 Note 2	LSB
			V <sub>DD</sub> = 3 V			±1.5 <sup>Note 2</sup>	LSB
Analog input voltage	VAIN			0		VDD	V

**Notes 1.** Excludes quantization error ( $\pm 1/2$  LSB).

2. This is the characteristic evaluation value plus or minus 3. These values are not used in the shipping inspection.

#### 2.6.2 SPOR circuit characteristics

#### $(T_A = -40 \text{ to } +85^\circ \text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection supply voltage	VSPOR0	Power supply rise time	4.08	4.28	4.45	V
		Power supply fall time	4.00	4.20	4.37	V
	VSPOR1	Power supply rise time	2.76	2.90	3.02	V
		Power supply fall time	2.70	2.84	2.96	V
	VSPOR2	Power supply rise time	2.44	2.57	2.68	V
		Power supply fall time	2.40	2.52	2.62	V
	<b>V</b> SPOR3	Power supply rise time	2.05	2.16	2.25	V
		Power supply fall time	2.00	2.11	2.20	V
Minimum pulse width Note	Tspw		300			μs

Note Time required for the reset operation by the SPOR when VDD becomes under VSPDR.

#### 2.6.3 Power supply voltage rising slope characteristics

#### $(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms



## 2.7 Flash Memory Programming Characteristics

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit	
Code flash memory rewritable times Notes 1, 2, 3	Cerwr	Retained for 20 years.	T <sub>A</sub> = + 85°C	1000			Times	

# $(T_A = 0 \text{ to } + 40^{\circ}\text{C}, 4.5 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

- **Notes 1.** 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
  - 2. When using flash memory programmer.
  - **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

#### 2.8 Dedicated Flash Memory Programmer Communication (UART)

#### $(T_A = 0 \text{ to } + 40^{\circ}\text{C}, 4.5 \text{ V} \le V_{DD} \le 5.5\text{V}, \text{ V}_{SS} = 0 \text{ V})$

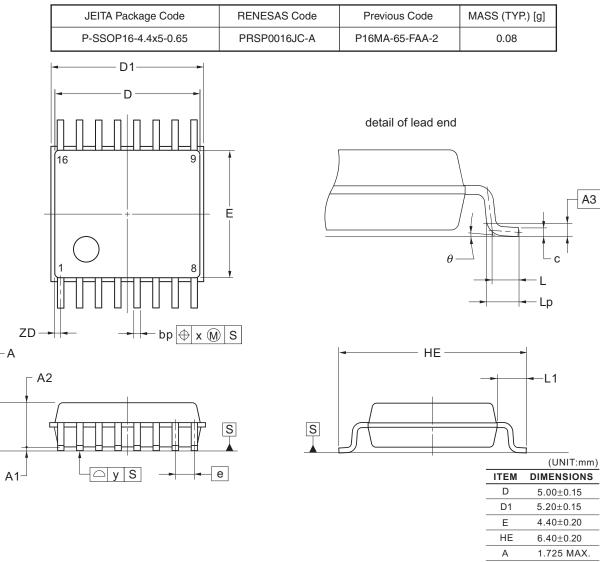
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate				115,200		bps

**Remark** The transfer rate during flash memory programming is fixed to 115,200 bps.



# 3.2 16-pin products

R5F10Y47ASP, R5F10Y46ASP, R5F10Y44ASP



ITEM	DIMENSIONS
D	5.00±0.15
D1	5.20±0.15
E	4.40±0.20
HE	6.40±0.20
А	1.725 MAX.
A1	0.125±0.05
A2	1.50
A3	0.25
е	0.65
bp	$0.22 \pm 0.08 - 0.07$
С	$0.15 \pm 0.03 \\ -0.04$
L	0.50
Lp	$0.60 {\pm} 0.10$
L1	1.00±0.20
х	0.13
У	0.10
θ	$3^{\circ} \frac{+5^{\circ}}{-3^{\circ}}$
ZD	0.325

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# RL78/G10 Data Sheet

		Description		
Rev.	Date	Page	Summary	
1.00	Apr 15, 2013	-	First Edition issued	

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SuperFlash is a registered trademark of Silicon Storage Technology, Inc. in several countries including the United States and Japan.

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#### NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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